

60 V, 320 mA N-channel Trench MOSFET Rev. 1 — 12 August 2011

Product data sheet

Product profile 1.

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 1.5 kV
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver

- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|--------------|-----|-----|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | - | - | 60 | V |
| V_{GS} | gate-source voltage | | -20 | - | 20 | V |
| I_D | drain current | V_{GS} = 10 V; T_{amb} = 25 °C | <u>[1]</u> - | - | 320 | mA |
| Static chara | acteristics | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 10 V; I_{D} = 320 mA; T_{j} = 25 °C | - | 1 | 1.6 | Ω |

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

Table 2. Pinning information

| | _ | , | | |
|-----|--------|-------------|---------------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | | |
| 2 | S | source | 3 | D |
| 3 | D | drain | 1 ☐ ☐ 2 SOT323 (SC-70) | G S 017aaa255 |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| BSS138BKW | SC-70 | plastic surface-mounted package; 3 leads | SOT323 |

4. Marking

Table 4. Marking codes

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| BSS138BKW | AD% |

^{[1] % =} placeholder for manufacturing site code.

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------------|---|--------------|------|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | - | 60 | V |
| V_{GS} | gate-source voltage | | -20 | 20 | V |
| I_D | drain current | V_{GS} = 10 V; T_{amb} = 25 °C | <u>[1]</u> _ | 320 | mA |
| | | V _{GS} = 10 V; T _{amb} = 100 °C | <u>[1]</u> _ | 210 | mA |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$ | - | 1.2 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] _ | 260 | mW |
| | | _ | [1] _ | 310 | mW |
| | | T _{sp} = 25 °C | - | 830 | mW |
| Tj | junction temperature | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | -55 | 150 | °C |
| T _{stg} | storage temperature | | -65 | 150 | °C |
| Source-drai | n diode | | | | |
| Is | source current | T _{amb} = 25 °C | <u>[1]</u> _ | 320 | mA |
| ESD maxim | um rating | | | | |
| V _{ESD} | electrostatic discharge voltage | НВМ | [3] _ | 1500 | V |
| | | | | | |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

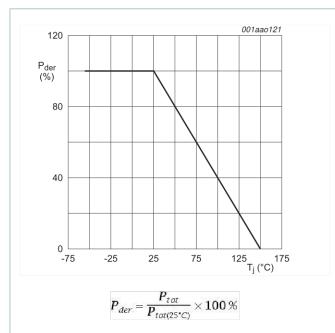


Fig 1. Normalized total power dissipation as a function of junction temperature

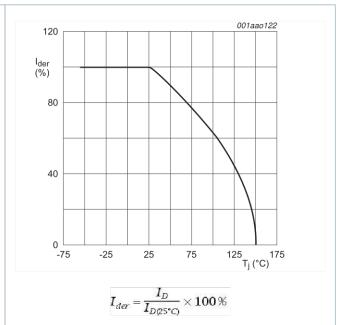
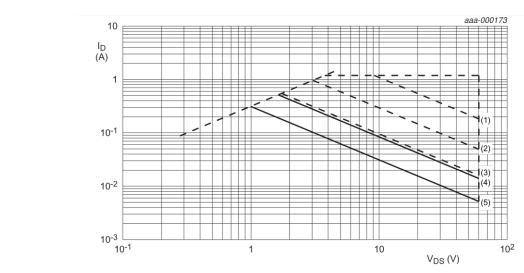


Fig 2. Normalized continuous drain current as a function of junction temperature

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I_{DM} is a single pulse

- (1) $t_p = 1 \text{ ms}$
- (2) $t_p = 10 \text{ ms}$
- (3) $t_p = 100 \text{ ms}$
- (4) DC; T_{sp} = 25 °C
- (5) DC; T_{amb} = 25 °C; 1 cm² drain mounting pad

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter Conditions | Min | Тур | Max | Unit |
|----------------------|---|-------|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient in free air | [1] - | 415 | 480 | K/W |
| | | [2] _ | 350 | 400 | K/W |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | - | - | 150 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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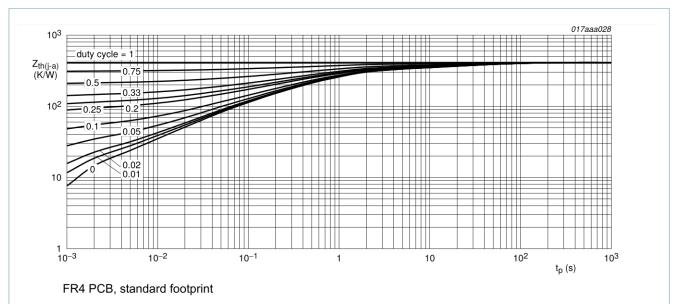


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

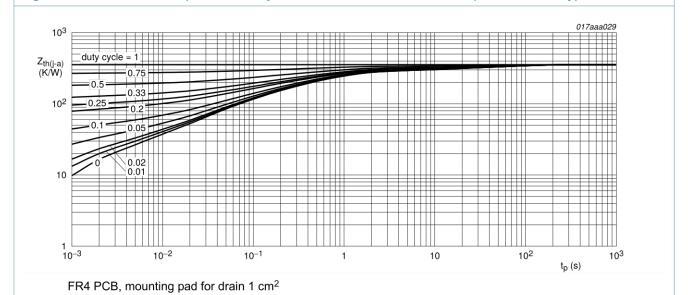


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

| Table 7. | Characteristics | | | | | |
|---------------------|-----------------------------------|---|------|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | racteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | 60 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | 0.48 | 1.1 | 1.6 | V |
| I _{DSS} | drain leakage current | $V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | - | 1 | μΑ |
| | | $V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$ | - | - | 10 | μΑ |
| I _{GSS} | gate leakage current | V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 10 | μΑ |
| | | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | - | 10 | μΑ |
| | | V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 1 | μΑ |
| | | $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | - | 1 | μΑ |
| R _{DSon} | drain-source on-state | V_{GS} = 10 V; I_{D} = 320 mA; T_{j} = 25 °C | - | 1 | 1.6 | Ω |
| | resistance | V_{GS} = 10 V; I_{D} = 320 mA; T_{j} = 150 °C | - | 2 | 3.2 | Ω |
| | | V_{GS} = 4.5 V; I_{D} = 200 mA; T_{j} = 25 °C | - | 1.1 | 2.2 | Ω |
| | | V_{GS} = 2.5 V; I_{D} = 10 mA; T_{j} = 25 °C | - | 1.4 | 6.5 | Ω |
| 9 _{fs} | forward transconductance | V_{DS} = 10 V; I_{D} = 200 mA; T_{j} = 25 °C | - | 700 | - | mS |
| Dynamic | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | V_{DS} = 30 V; I_{D} = 300 mA; V_{GS} = 4.5 V; | - | 0.6 | 0.7 | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C | - | 0.1 | - | nC |
| Q_{GD} | gate-drain charge | | - | 0.2 | - | nC |
| C _{iss} | input capacitance | $V_{DS} = 10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$ | - | 42 | 56 | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 7 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 4 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 40 V; R_{L} = 250 Ω ; V_{GS} = 10 V; | - | 5 | 10 | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 5 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 38 | 76 | ns |
| t _f | fall time | | - | 20 | - | ns |
| Source-di | ain diode | | | | | |
| V _{SD} | source-drain voltage | I_S = 300 mA; V_{GS} = 0 V; T_i = 25 °C | 0.47 | 0.8 | 1.2 | V |

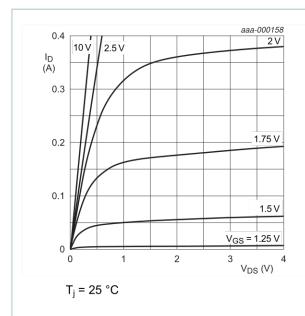
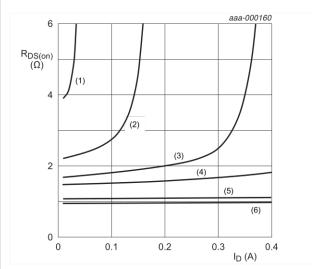


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T_i = 25 °C

 $(1) V_{GS} = 1.5 V$

(2) $V_{GS} = 1.75 V$

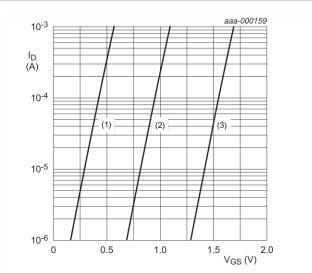
 $(3) V_{GS} = 2.0 V$

 $(4) V_{GS} = 2.25 V$

 $(5) V_{GS} = 4.5 V$

(6) $V_{GS} = 10 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



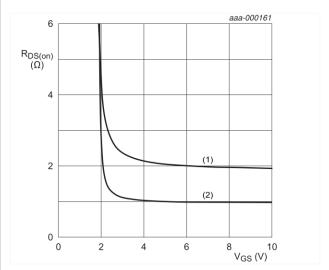
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage

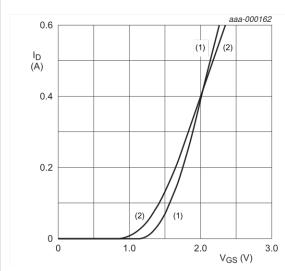


 $I_D = 300 \text{ mA}$

(1) $T_j = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_j = 25 \, ^{\circ}C$$

(2)
$$T_i = 150 \, ^{\circ}C$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

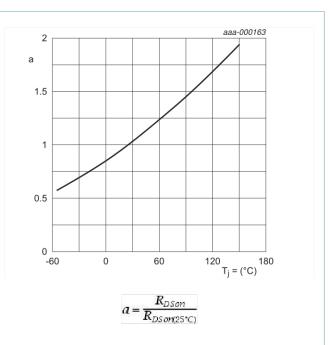
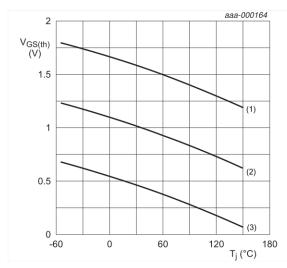


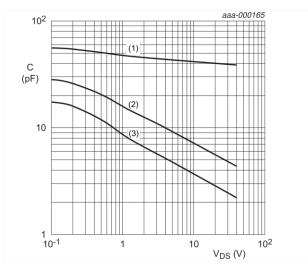
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$

- (1) C_{iss}
- (2) Coss
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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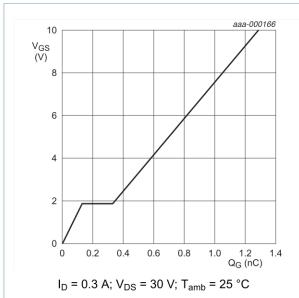


Fig 14. Gate-source voltage as a function of gate charge; typical values

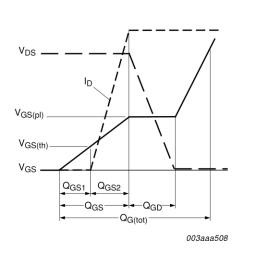
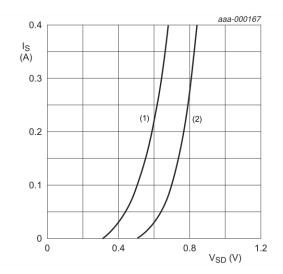


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

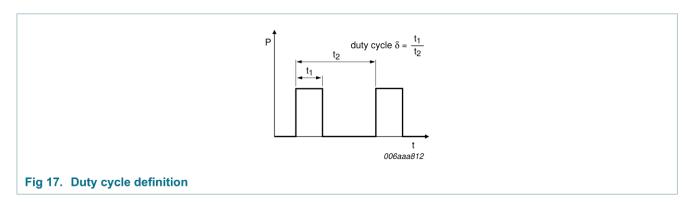
(1) $T_i = 150 \,^{\circ}\text{C}$

(2) $T_j = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

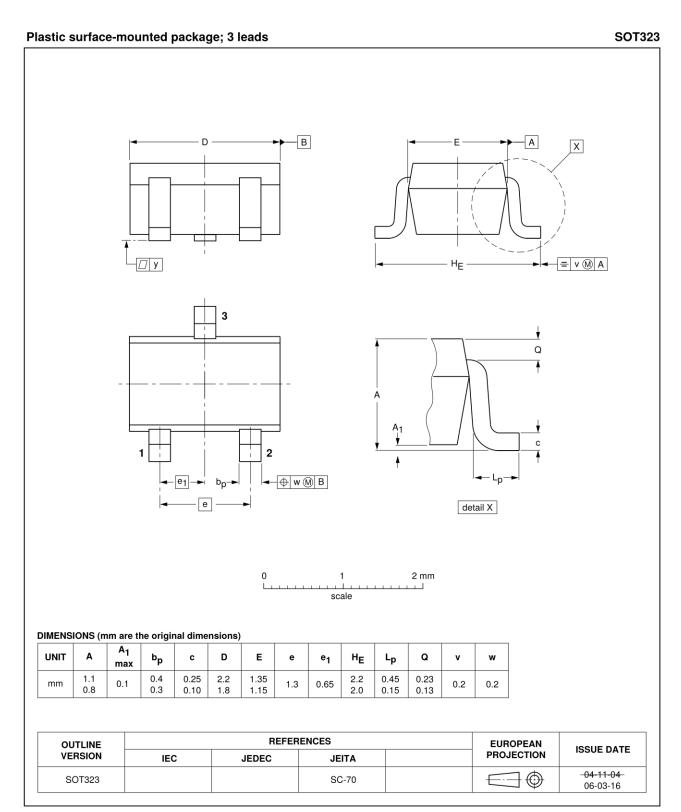
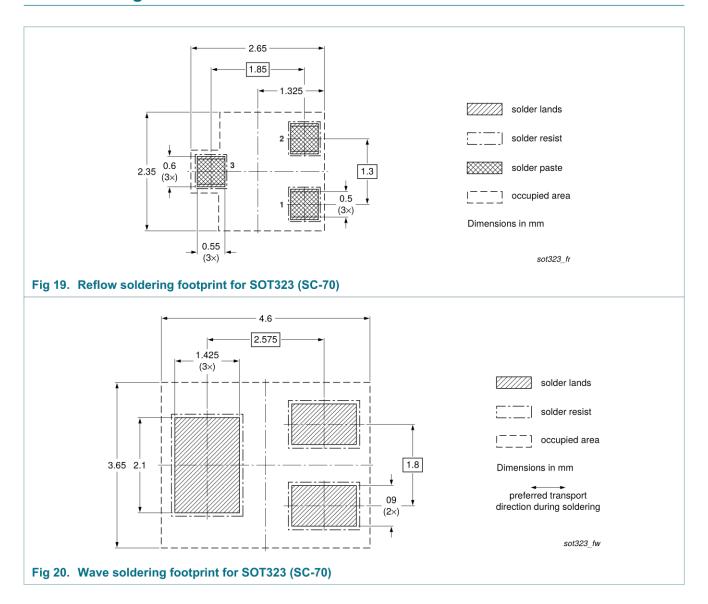


Fig 18. Package outline SOT323 (SC-70)

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10. Soldering



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11. Revision history

Table 8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| BSS138BKW v.1 | 20110812 | Product data sheet | - | - |

12. Legal information

12.1 Data sheet status

| Document status [1] [2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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